

NTD24N06-001 Information



For Reference Only

Part Number NTD24N06-001
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 24A IPAK

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTD24N06-001 Specifications

Manufacturer Part Number NTD24N06-001 Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 24A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 48nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.36W (Ta), 62.5W (Tj) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		
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Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 24A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 48nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.36W (Ta), 62.5W (Tj) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C24A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs48nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.36W (Ta), 62.5W (Tj)Rds On (Max) @ Id, Vgs42 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Package	TO-251-3 Short Leads, IPak, TO-251AA
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 24A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Supplier Device Package Package / Case MOSFET (Metal Oxide) 60V 60V 24A (Ta) 60V 24A (Ta) 4V @ 250μA 4V @ 250μA 48nC @ 10V 1200pF @ 25V ±20V FET Feature - Power Dissipation (Max) 1.36W (Ta), 62.5W (Tj) 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Through Hole	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C24A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs48nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.36W (Ta), 62.5W (Tj)Rds On (Max) @ Id, Vgs42 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature Supplier Device Package Package / Case 24A (Ta) 24A (Ta)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs48nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1200pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.36W (Ta), 62.5W (Tj)Rds On (Max) @ Id, Vgs42 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Found Temperature Supplier Device Package Package / Case 48nC @ 10V 1200pF @ 25V +20V FET (Feature) - - - - - - - - - - - - -	Current - Continuous Drain (Id) @ 25°C	24A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature John Charge (Qg) (Max) @ Vds 42 mOhm @ 10A, 10V Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1200pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.36W (Ta), 62.5W (Tj) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Gate Charge (Qg) (Max) @ Vgs	48nC @ 10V
FET Feature - Power Dissipation (Max) 1.36W (Ta), 62.5W (Tj) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Input Capacitance (Ciss) (Max) @ Vds	1200pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 42 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs42 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageI-PakPackage / CaseTO-251-3 Short Leads, IPak, TO-251AA	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Power Dissipation (Max)	1.36W (Ta), 62.5W (Tj)
Mounting Type Through Hole Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Rds On (Max) @ Id, Vgs	42 mOhm @ 10A, 10V
Supplier Device Package I-Pak Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA	Mounting Type	Through Hole
	Supplier Device Package	I-Pak
Report errors?	Package / Case	TO-251-3 Short Leads, IPak, TO-251AA
		Report errors?

NTD24N06-001 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD24N06-001 Payment Methods



















NTD24N06-001 Shipping Methods













If you have any question about NTD24N06-001, please do not hesitate to contact us!

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